Hui Fang

List of Publications by Year in Descending Order

58 papers	7,244 citations	33 h-index	59 g-index
59 ext. papers	8,150 ext. citations	9.9 avg, IF	5.57 L-index

#	Paper	IF	Citations
58	Hybrid Electrical and Optical Neural Interfaces. *Journal of Micromechanics and Microengineering*, **2021**, 31,	2	2
57	Crosstalk in Polymer Microelectrode Arrays. *Nano Research*, **2021**, 14, 3240-3247	10	0
56	Synergistic enhancement of thermal conductivity by addition of graphene nanoplatelets to three-dimensional boron nitride scaffolds for polyamide 6 composites. *Polymer Engineering and Science*, **2021**, 61, 1415-1426	2.3	0
55	Radiation-Induced Lymphopenia Predicts Poorer Prognosis in Patients With Breast Cancer: A Post Hoc Analysis of a Randomized Controlled Trial of Postmastectomy Hypofractionated Radiation Therapy. *International Journal of Radiation Oncology Biology Physics*, **2020**, 108, 277-285	4	16
54	Development of a neural interface for high-definition, long-term recording in rodents and nonhuman primates. *Science Translational Medicine*, **2020**, 12,	17.5	64
53	Mechanics of Regular-Shape Nanomeshes for Transparent and Stretchable Devices. *Journal of Applied Mechanics, Transactions ASME*, **2020**, 87,	2.7	4
52	Nomogram predicting survival as a selection criterion for postmastectomy radiotherapy in patients with T1 to T2 breast cancer with 1 to 3 positive lymph nodes. *Cancer*, **2020**, 126 Suppl 16, 3857-3866	6.4	3
51	Preface to the Special Issue on Flexible Materials and Structures for Bioengineering, Sensing, and Energy Applications. *Journal of Semiconductors*, **2020**, 41, 040101	2.3	1
50	Microelectrode Arrays: Transparent, Flexible, Penetrating Microelectrode Arrays with Capabilities of Single-Unit Electrophysiology (Adv. Biosys. 3/2019). *Advanced Biology*, **2019**, 3, 1970033	3.5	
49	Nanomeshed Si nanomembranes. *Npj Flexible Electronics*, **2019**, 3,	10.7	9
48	Design of atomically-thin-body field-effect sensors and pattern recognition neural networks for ultra-sensitive and intelligent trace explosive detection. *2D Materials*, **2019**, 6, 044002	5.9	
47	Flexible electronic/optoelectronic microsystems with scalable designs for chronic biointegration. *Proceedings of the National Academy of Sciences of the United States of America*, **2019**, 116, 15398-15406	11.5	44
46	Transparent, Flexible, Penetrating Microelectrode Arrays with Capabilities of Single-Unit Electrophysiology. *Advanced Biology*, **2019**, 3, e1800276	3.5	19
45	Transferred, Ultrathin Oxide Bilayers as Biofluid Barriers for Flexible Electronic Implants. *Advanced Functional Materials*, **2018**, 28, 1702284	15.6	36
44	Ultrathin Trilayer Assemblies as Long-Lived Barriers against Water and Ion Penetration in Flexible Bioelectronic Systems. *ACS Nano*, **2018**, 12, 10317-10326	16.7	33
43	Imaging Sodium Flux during Action Potentials in Neurons with Fluorescent Nanosensors and Transparent Microelectrodes. *ACS Sensors*, **2018**, 3, 2499-2505	9.2	12
42	Transparent arrays of bilayer-nanomesh microelectrodes for simultaneous electrophysiology and two-photon imaging in the brain. *Science Advances*, **2018**, 4, eaat0626	14.3	66

41	Wafer-scale, stretchable nanomeshes from an ultrathin-support-layer assisted transfer. *Applied Physics Letters*, **2018**, 112, 263101	3.4	8
40	Capacitively Coupled Arrays of Multiplexed Flexible Silicon Transistors for Long-Term Cardiac Electrophysiology. *Nature Biomedical Engineering*, **2017**, 1,	19	163
39	Graphene and related two-dimensional materials: Structure-property relationships for electronics and optoelectronics. *Applied Physics Reviews*, **2017**, 4, 021306	17.3	368
38	Transparent Electrophysiology Microelectrodes and Interconnects from Metal Nanomesh. *ACS Nano*, **2017**, 11, 4365-4372	16.7	38
37	Bilayer Nanomesh Structures for Transparent Recording and Stimulating Microelectrodes. *Advanced Functional Materials*, **2017**, 27, 1704117	15.6	36
36	Thin, Transferred Layers of Silicon Dioxide and Silicon Nitride as Water and Ion Barriers for Implantable Flexible Electronic Systems. *Advanced Electronic Materials*, **2017**, 3, 1700077	6.4	44
35	. *IEEE Transactions on Electron Devices*, **2017**, 64, 3443-3451	2.9	12
34	Materials and processing approaches for foundry-compatible transient electronics. *Proceedings of the National Academy of Sciences of the United States of America*, **2017**, 114, E5522-E5529	11.5	70
33	2-D InAs XOI FETs **2017**, 185-195		
32	Ultrathin, transferred layers of thermally grown silicon dioxide as biofluid barriers for biointegrated flexible electronic systems. *Proceedings of the National Academy of Sciences of the United States of America*, **2016**, 113, 11682-11687	11.5	133
31	Possible contribution of IMRT in postoperative radiochemotherapy for rectal cancer: analysis on 1798 patients by prediction model. *Oncotarget*, **2016**, 7, 46536-46544	3.3	1
30	Bioresorbable silicon electronics for transient spatiotemporal mapping of electrical activity from the cerebral cortex. *Nature Materials*, **2016**, 15, 782-791	27	296
29	Optics and Nonlinear Buckling Mechanics in Large-Area, Highly Stretchable Arrays of Plasmonic Nanostructures. *ACS Nano*, **2015**, 9, 5968-75	16.7	73
28	2D layered materials: From materials properties to device applications **2015**,		8
27	Dual-gated MoS2/WSe2 van der Waals tunnel diodes and transistors. *ACS Nano*, **2015**, 9, 2071-9	16.7	441
26	Strong interlayer coupling in van der Waals heterostructures built from single-layer chalcogenides. *Proceedings of the National Academy of Sciences of the United States of America*, **2014**, 111, 6198-202	11.5	803
25	MoS P-type transistors and diodes enabled by high work function MoOx contacts. *Nano Letters*, **2014**, 14, 1337-42	11.5	419
24	Series resistance and mobility in mechanically-exfoliated layered transition metal dichalcogenide MOSFETs **2014**,		2

23	High-gain inverters based on WSe2 complementary field-effect transistors. *ACS Nano*, **2014**, 8, 4948-53	16.7	249
22	Strain-induced indirect to direct bandgap transition in multilayer WSe2. *Nano Letters*, **2014**, 14, 4592-7	11.5	415
21	High quality interfaces of InAs-on-insulator field-effect transistors with ZrO2 gate dielectrics. *Applied Physics Letters*, **2013**, 102, 153513	3.4	29
20	Degenerate n-doping of few-layer transition metal dichalcogenides by potassium. *Nano Letters*, **2013**, 13, 1991-5	11.5	567
19	Near-ideal electrical properties of InAs/WSe2 van der Waals heterojunction diodes. *Applied Physics Letters*, **2013**, 102, 242101	3.4	64
18	Quantum of optical absorption in two-dimensional semiconductors. *Proceedings of the National Academy of Sciences of the United States of America*, **2013**, 110, 11688-91	11.5	61
17	Ultrathin-Body High-Mobility InAsSb-on-Insulator Field-Effect Transistors. *IEEE Electron Device Letters*, **2012**, 33, 504-506	4.4	22
16	Nanoscale InGaSb heterostructure membranes on Si substrates for high hole mobility transistors. *Nano Letters*, **2012**, 12, 2060-6	11.5	74
15	Self-aligned, extremely high frequency III-V metal-oxide-semiconductor field-effect transistors on rigid and flexible substrates. *Nano Letters*, **2012**, 12, 4140-5	11.5	67
14	III-V complementary metal-oxide-semiconductor electronics on silicon substrates. *Nano Letters*, **2012**, 12, 3592-5	11.5	74
13	Quantum Size Effects on the Chemical Sensing Performance of Two-Dimensional Semiconductors. *Journal of Physical Chemistry C*, **2012**, 116, 9750-9754	3.8	36
12	High-performance single layered WSe□-FETs with chemically doped contacts. *Nano Letters*, **2012**, 12, 3788-92	11.5	1322
11	Quantum confinement effects in nanoscale-thickness InAs membranes. *Nano Letters*, **2011**, 11, 5008-12	11.5	88
10	Thermoelectric Performance of Zn and Ge Co-Doped In2O3 Fine-Grained Ceramics by the Spark Plasma Sintering. *Journal of the American Ceramic Society*, **2011**, 94, 2279-2281	3.8	13
9	Nanoscale semiconductor "X" on substrate "Y"--processes, devices, and applications. *Advanced Materials*, **2011**, 23, 3115-27	24	39
8	Benchmarking the performance of ultrathin body InAs-on-insulator transistors as a function of body thickness. *Applied Physics Letters*, **2011**, 99, 103507	3.4	37
7	Strain engineering of epitaxially transferred, ultrathin layers of III-V semiconductor on insulator. *Applied Physics Letters*, **2011**, 98, 012111	3.4	19
6	High-Temperature Thermoelectric Behaviors of Fine-Grained Gd-Doped CaMnO3 Ceramics. *Journal of the American Ceramic Society*, **2010**, 93, 2121-2124	3.8	58

5	Ultrathin compound semiconductor on insulator layers for high-performance nanoscale transistors. *Nature*, **2010**, 468, 286-9	50.4	327
4	Shape-controlled synthesis of single-crystalline nanopillar arrays by template-assisted vapor-liquid-solid process. *Journal of the American Chemical Society*, **2010**, 132, 13972-4	16.4	28
3	Metal-catalyzed crystallization of amorphous carbon to graphene. *Applied Physics Letters*, **2010**, 96, 063110	3.4	208
2	Fabrication of slantingly-aligned silicon nanowire arrays for solar cell applications. *Nanotechnology*, **2008**, 19, 255703	3.4	194
1	Topochemical Synthesis of a High-Aspect-Ratio Platelet NaNbO3 Template. *Journal of the American Ceramic Society*, **2007**, 90, 2399-2403	3.8	29